Photomodulated reflectance measurement technique for implantation tilt angle monitoring

f f^ao 'Mwp Semilab Co. Ltd.r Budapest, Hungary adam.kun@semilab.hu

Leonard M. Rubin Axcelis Technologies, Beverly, MA USA Leonard.Rubin@axcelis.com

Qtuqn(c'Cm ^a uk Semilab Co. Ltd.r Budapest, Hungary orsolya.almasi@semilab.hu implants and to suppress the device parametric variation at high angle halo implants [2]. These requirements are relaxed y j gp" s wcf " o qf g" ko r rcpw" ctg" cr r rkgf " y kj " ; 2Å wafer rotation. For sub-65 nm source-drain extension (SDE) ko r rcpw" dgco "uvgtkpi " o ww" dg" eqpvtqmgf " vq" >2047Å for ukpi rg" vgr "UF G"cpf "3Åfor quad mode SDE step.

Keeping ion beam angle in precise control in production or after maintenance is a key and requires high quality tool monitoring metrology [6]. In our paper we present the excellent tilt angle measurement capabilities of PMR-3000S in-line implantation monitoring tool.

II. EXPERIMENTAL

A. Photo-modulated optical reflectivity

Photo-modulated Optical Reflectivity measurement (PMR) dcugf "qp"vj g"r j gpqo gpqp"qh"Ecttlgt "Knwo kpcvkqp \hat{I} "ku"cp" excellent non-contact, non-destructive technology for implantation monitoring on as-implanted pre-annealed production wafers with a measurement spot size smaller vj cp"5" $\hat{U}o$ 0

The working principle of the measurement is based on the known phenomenon that optical excitation of a sample (surface) results in the change of its reflectance. In the case of semiconductor samples, the mechanisms responsible for the reflectance change include the creation of excess carriers and heat gradient due to the excitation. The PMR measurement process focuses mainly to the former thus the

optical excitation is provided by an intensity modula2(n)6(t13 Tm0 g0 G[(2(7.1 Tm8E)6(e))-10(h)-5(u)6(s)3(QTm0(y)6(n)6()-351

B. PMR-3000 tool

SEMILAB PMR-3000 shown in Fig. 4. is an ion implantation dose monitoring unit for in-line ion implantation monitoring use preceding the thermal annealing process step. PMR is sensitive in a wide range of implant dose level $(5*10^{10}: 5, 5*10^{16} \text{ ion/cm}^2)$.

The use of a built-in laser light intensity stabilization system results in an enhanced PMR signal repeatability (3 < 0.15%) and stability (3 < 0.45%). (Values are valid for PMR reference

The ion implant tilt angle sensitivity of the PMR tool wa